

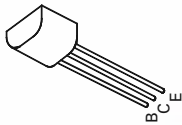
PNP SILICON PLANAR
MEDIUM POWER TRANSISTOR

FXT755

ISSUE 1 – FEB 94

FEATURES

- * 150 Volt V_{CE}
- * 1 Amp continuous current
- * Low saturation voltage
- * P_{tot} = 1 Watt



E-Line
TO92 Compatible

REFER TO ZTX755 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-150			V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-150			V	$I_C = -10\text{mA}, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CE} = -125\text{V}, I_E = 0$
Emitter Cut-Off Current	I_{EBO}			-100	nA	$V_{EB} = -3\text{V}, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5 -0.5	V V	$I_C = -500\text{mA}, I_B = -50\text{mA}^*$ $I_C = -1\text{A}, I_B = -200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C = -500\text{mA}, I_B = -50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -500\text{mA}, V_{CE} = -5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	50 50 20				$I_C = -10\text{mA}, V_{CE} = -5\text{V}$ $I_C = -500\text{mA}, V_{CE} = -5\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -5\text{V}^*$
Transition Frequency	f_T	30			MHz	$I_C = -10\text{mA}, V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}			20	pF	$V_{CE} = -20\text{V}, f = 1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$

查询FXT755供应商

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